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(54) **Title:** CONTROL OF ANISOTROPIC DEFORMATION WITH DIRECTIONAL STRESS MODULATION FOR DEVICE MANUFACTURING

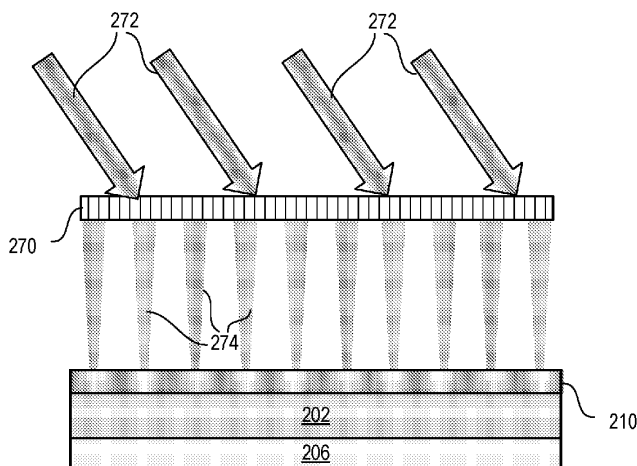


FIG. 2L

(57) **Abstract:** Disclosed systems and techniques are directed to improvement of semiconductor manufacturing. In one disclosed embodiment, the disclosed techniques include identifying an anisotropic deformation of a substrate, the substrate supporting one or more deposited films and forming, responsive to the identified anisotropic deformation, a stress-compensation layer (SCL) on the substrate. The disclosed techniques further include subjecting the SCL to a stress-mitigation beam to induce a directionally-modulated pattern of stress in the SCL, the directionally-modulated pattern of stress in the SCL causing mitigation of the anisotropic deformation of the substrate.

[Continued on next page]

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